



General Description

The QM3024S is the highest performance trench N-ch MOSFETs with extreme high cell density, which provide excellent R_{DS(on)} and gate charge for most of the synchronous buck converter applications.

The QM3024S meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

Absolute Maximum Ratings

Symbol	Parameter	Rating		Units
		10s	Steady State	
V _{DS}	Drain-Source Voltage	30		V
V _{GS}	Gate-Source Voltage	±20		V
I _D @T _A =25°C	Continuous Drain Current, V _{GS} @ 10V ¹	13.4	10.3	A
I _D @T _A =70°C	Continuous Drain Current, V _{GS} @ 10V ¹	10.7	8.2	A
I _{DM}	Pulsed Drain Current ²	52		A
EAS	Single Pulse Avalanche Energy ³	130		mJ
I _{AS}	Avalanche Current	34		A
P _D @T _A =25°C	Total Power Dissipation ⁴	2.5	1.5	W
P _D @T _A =70°C	Total Power Dissipation ⁴	1.6	0.94	W
T _{STG}	Storage Temperature Range	-55 to 150		°C
T _J	Operating Junction Temperature Range	-55 to 150		°C

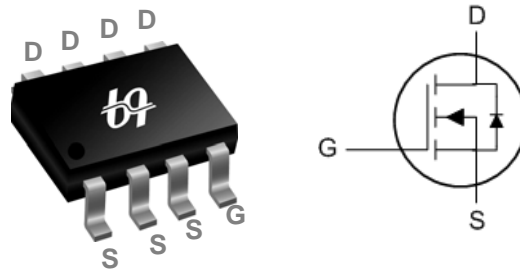
Product Summary

BVDSS	R _{DS(on)}	I _D
30V	9 mΩ	10.3A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

SOP8 Pin Configuration



Symbol

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-ambient ¹	---	85	°C/W
R _{θJA}	Thermal Resistance Junction-Ambient ¹ (t ≤ 10s)	---	50	°C/W
R _{θJC}	Thermal Resistance Junction-Case ¹	---	25	°C/W

Electrical Characteristics ($T_J=25\text{ }^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30	35	---	V
$\Delta BV_{DSS}/\Delta T_J$	BVDSS Temperature Coefficient	Reference to $25\text{ }^\circ\text{C}$, $I_D=1mA$	---	0.024	---	V/ $^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V, I_D=10A$	---	7.2	9	m Ω
		$V_{GS}=4.5V, I_D=8A$	---	10.5	13.5	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2	1.5	2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-3.5	---	mV/ $^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=24V, V_{GS}=0V, T_J=25\text{ }^\circ\text{C}$	---	---	1	μA
		$V_{DS}=24V, V_{GS}=0V, T_J=55\text{ }^\circ\text{C}$	---	---	5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=5V, I_D=10A$	---	35.4	---	S
R_g	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1MHz$	---	1.45	2.4	Ω
Q_g	Total Gate Charge (4.5V)	$V_{DS}=15V, V_{GS}=4.5V, I_D=10A$	---	10.6	14.8	nC
Q_{gs}	Gate-Source Charge		---	4.0	5.6	
Q_{gd}	Gate-Drain Charge		---	4.1	5.7	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=15V, V_{GS}=10V, R_G=3.3\Omega, I_D=10A$	---	5.8	11.6	ns
T_r	Rise Time		---	61	110	
$T_{d(off)}$	Turn-Off Delay Time		---	23.6	47	
T_f	Fall Time		---	7.6	15	
C_{iss}	Input Capacitance	$V_{DS}=15V, V_{GS}=0V, f=1MHz$	---	1127	1578	μF
C_{oss}	Output Capacitance		---	194	272	
C_{riss}	Reverse Transfer Capacitance		---	77	108	

Guaranteed Avalanche Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
EAS	Single Pulse Avalanche Energy ⁵	$V_{DD}=25V, L=0.1mH, I_{AS}=20A$	45	---	---	mJ

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,6}	$V_G=V_D=0V, \text{Force Current}$	---	---	10.3	A
I_{SM}	Pulsed Source Current ^{2,6}		---	---	52	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=1A, T_J=25\text{ }^\circ\text{C}$	---	---	1	V
t_{rr}	Reverse Recovery Time	$I_F=10A, di/dt=100A/\mu s, T_J=25\text{ }^\circ\text{C}$	---	14.1	---	nS
Q_{rr}	Reverse Recovery Charge		---	5.9	---	nC

Note :

- The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- The EAS data shows Max. rating. The test condition is $V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=34A$
- The power dissipation is limited by $150\text{ }^\circ\text{C}$ junction temperature
- The Min. value is 100% EAS tested guarantee.
- The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.

Typical Characteristics

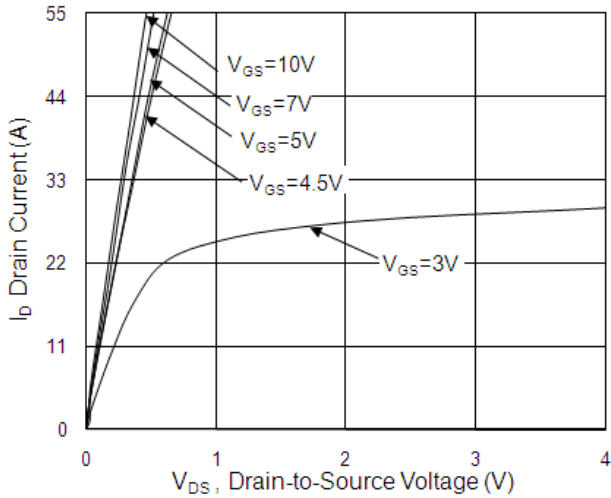


Fig.1 Typical Output Characteristics

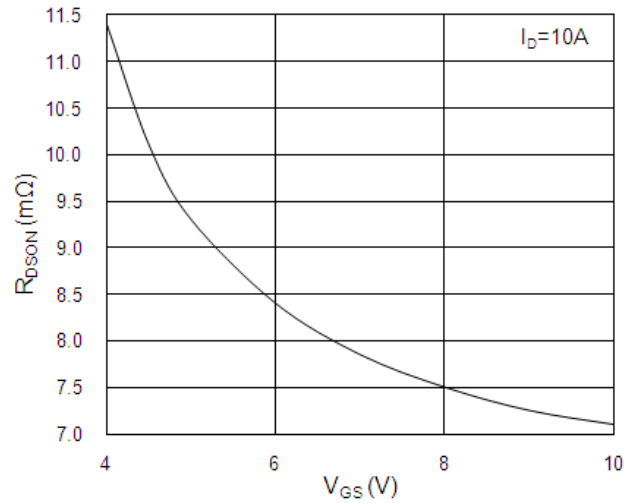


Fig.2 On-Resistance vs. Gate-Source

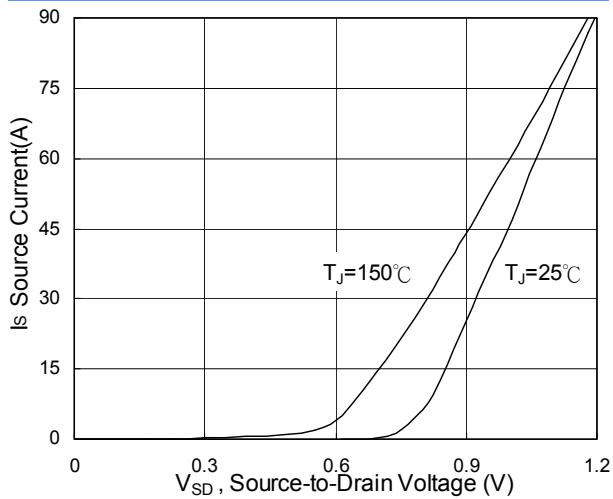


Fig.3 Forward Characteristics of Reverse

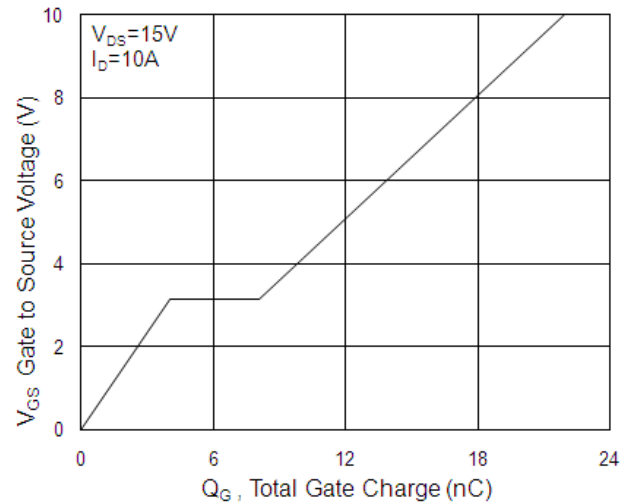


Fig.4 Gate-Charge Characteristics

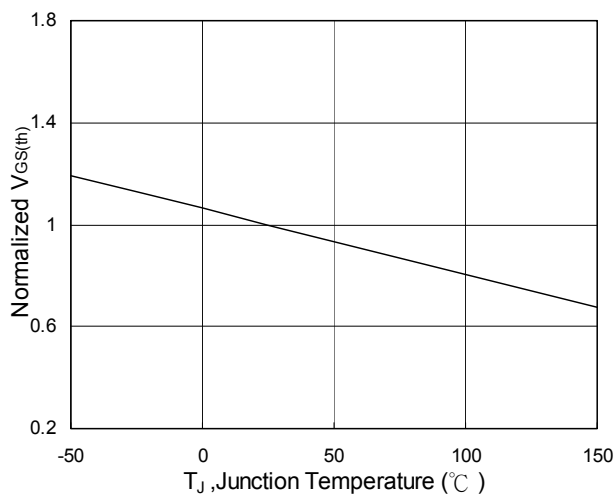


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

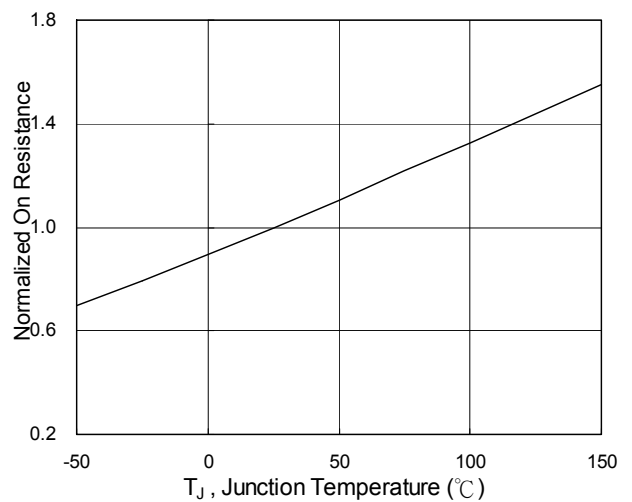


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

N-Ch 30V Fast Switching MOSFETs

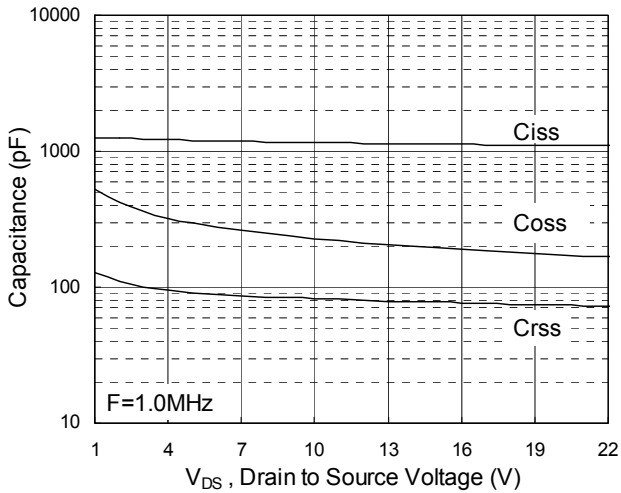


Fig.7 Capacitance

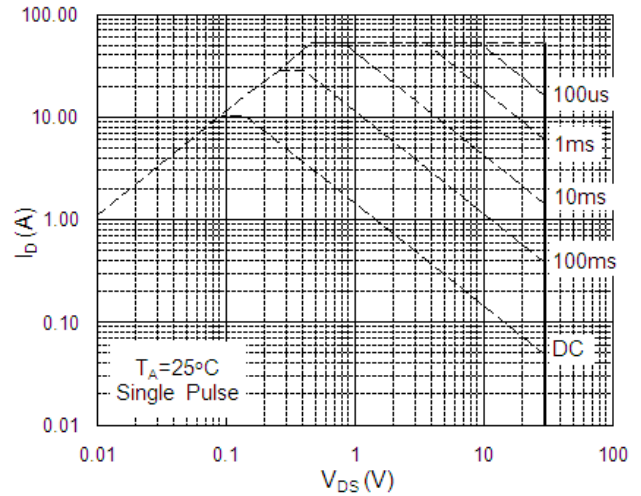


Fig.8 Safe Operating Area

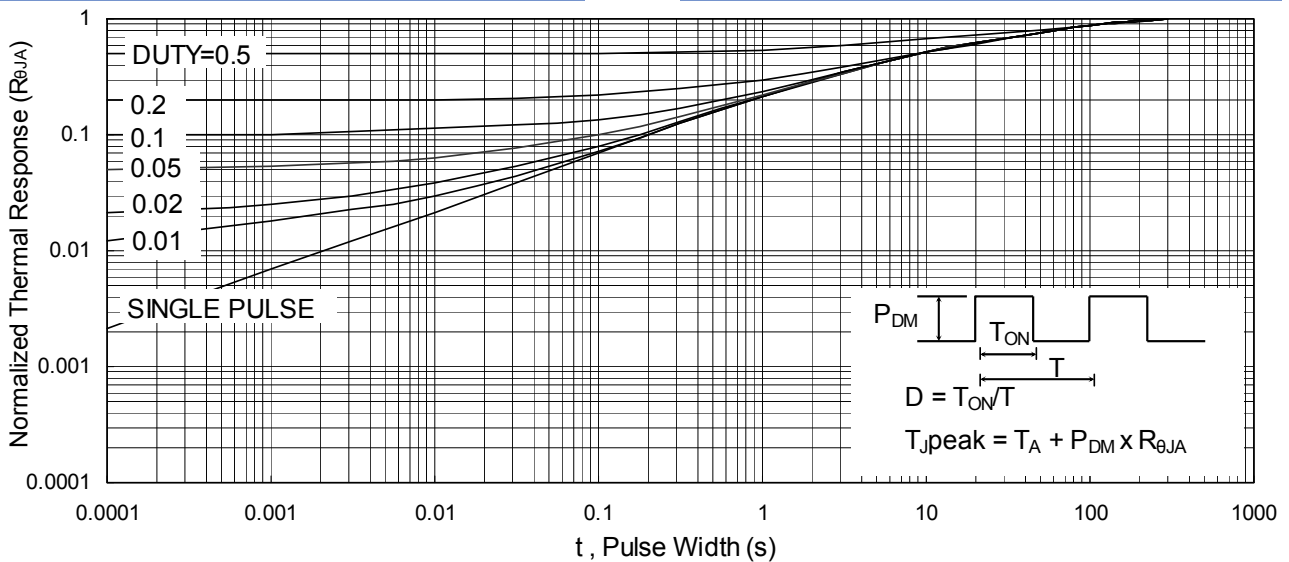


Fig.9 Normalized Maximum Transient Thermal Impedance

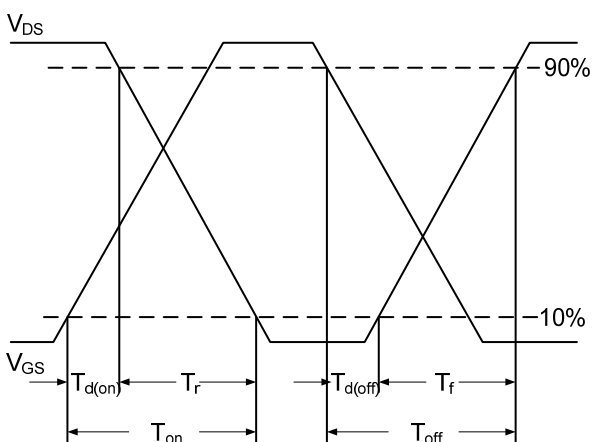


Fig.10 Switching Time Waveform

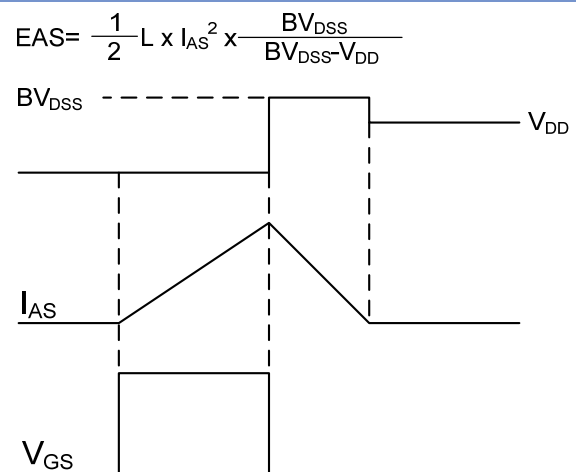


Fig.11 Unclamped Inductive Switching Waveform